Silicon PNP Power Transistors 2N6226 2N6227 2N6228

DESCRIPTION

- With TO-3 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- For high power audio;stepping motor and other linear applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6226	Open emitter	-100	V
		2N6227		-120	
		2N6228		-140	
V_{CEO}	Collector-emitter voltage	2N6226	Open base	-100	V
		2N6227		-120	
		2N6228		-140	
V_{EBO}	Emitter-base voltage		Open collector	-7	V
I_C	Collector current			-6	A
P_D	Total power dissipation		T_C=25℃	150	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	0.92	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N6226	I_C=-0.2A ;I_B=0	-100			V
		2N6227		-120			
		2N6228		-140			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-4A; I_B=-0.4A			-1.2	V
V_{BE}	Base-emitter on voltage		I_C=-3A ; V_{CE}=-2V			-1.8	V
I_{CEO}	Collector cut-off current		V_{CE}=Rated V_{CEO}; I_B=0			-5.0	mA
I_{CBO}	Collector cut-off current		V_{CB}=Rated V_{CBO}; I_E=0			-1.0	mA
I_{EBO}	Emitter cut-off current		V_{EB}=-7V; I_C=0			-0.1	mA
h_{FE}	DC current gain	2N6226	I_C=-3A ; V_{CE}=-2V	25		100	
		2N6227		20		80	
		2N6228		15		60	
f_T	Transition frequency		I_C=-0.5A ; V_{CE}=-4V	1			MHz

PACKAGE OUTLINE

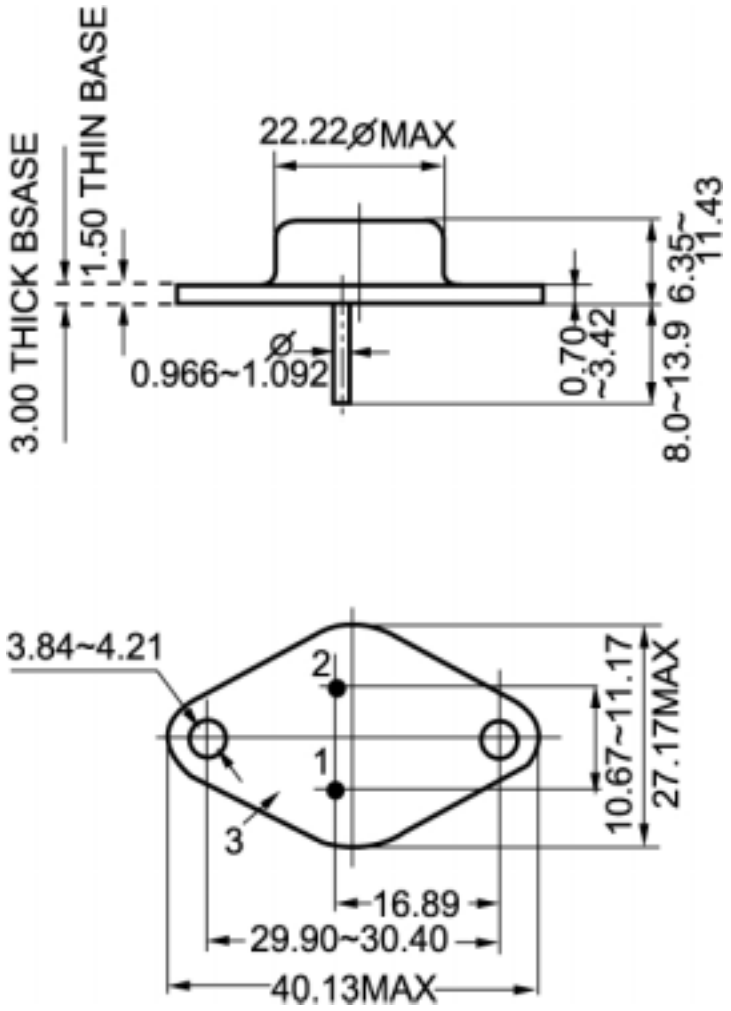

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)